XRPX Acc No: N89-073802
Washing and oxidising semiconductive wafer - by contacting wafer with supercritical carbon dioxide and then with carbon dioxide, etc.
Patent Assignee: HITACHI LTD (HITA)
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Main IPC	Week
JP 1045131	A	19890217	JP 87201720	A	19870814		198913 B

Priority Applications (No Type Date): JP 87201720 A 19870814
Patent Details:

Patent	Kind	Lan	Pg	Filing Notes	Application	Patent
JP 1045131	A		4			

Abstract (Basic): JP 1045131 A

Semiconductive wafer is brought into contact with supercritical carbon dioxide or liquefied carbon dioxide to be washed, and then semiconductive wafer is brought into contact with carbon dioxide including at least one kind of substance having oxygen, or supercritical carbon dioxide gas similar to carbon dioxide gas, to oxidise Si surface of semiconductive wafer.

Washing and oxidising are performed in one tank. Substance having O is O2, O3, H2O or H2O3. Supercritical carbon dioxide gas or liquefied carbon dioxide gas used in washing includes at least one kind of substance having O.

USE/ADVANTAGE - Number of times of contact with air in clean room, of semiconductive wafer can be reduced, so that contamination of wafer by air can be decreased, and yield rate in mfr. of semiconductor, can be improved. Washing and oxidising can be performed in one process, so that mfr. is simplified.

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Title Terms: WASHING; OXIDATION; SEMICONDUCTOR; WAFER; CONTACT; WAFER; SUPERCRITICAL; CARBON; DI; OXIDE; CARBON; DI; OXIDE
Derwent Class: E36; L03; U11
International Patent Class (Additional): B01D-011/04; H01L-021/31
File Segment: CPI; EPI
Manual Codes (CPI/A-N): E31-D02; E31-D03; E31-E; E31-N05C; L04-C09
Manual Codes (EPI/S-X): U11-C04A1; U11-C05B1
Chemical Fragment Codes (M3):
01 C101 C106 C108 C408 C530 C550 C730 C800 C801 C802 C803 C804 C805 C807 C810 M411 M782 M903 M904 M910 Q454 R01066-M R01732-M R01779-M R01887-M
Derwent Registry Numbers: 1066-U; 1732-U; 1779-U; 1887-U
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004453953
WPI Acc No: 85-280831/**198545**
Stripping-off organic coating-hardening films - such as photoresist-film of semiconductor wafers NoAbstract Dwg 0/2
Patent Assignee: HITACHI LTD (HITA)
Number of Countries: 001 Number of Patents: 002
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Main IPC	Week
JP 60192333	A	19850930	JP 8447653	A	19840313		198545 B
JP 89044013	B	19890925					198942

Priority Applications (No Type Date): JP 8447653 A 19840313
Patent Details:

Patent	Kind	Lan	Pg	Filing Notes	Application	Patent
JP 60192333	A		8			

Title Terms: STRIP; ORGANIC; COATING; HARDEN; FILM; PHOTORESIST; FILM;